







DRV8662 JAJSPD5C – JUNE 2011 – REVISED DECEMBER 2022

# DRV8662 昇圧コンバータを内蔵したピエゾ・ハプティクス・ドライバ

## 1 特長

- 高電圧ピエゾ・ハブティクス・ドライバ
  - 200V<sub>PP</sub>、300Hz で最大 100nF を駆動
  - 150V<sub>PP</sub>、300Hz で最大 150nF を駆動
  - 100V<sub>PP</sub>、300Hz で最大 330nF を駆動
  - 50V<sub>PP</sub>、300Hz で最大 680nF を駆動
  - 差動出力
- 昇圧コンバータ内蔵
  - 可変昇圧電圧
  - 可変電流制限
  - パワー FET およびダイオードを内蔵
  - 変圧器不要
- 1.5ms の高速なスタートアップ時間
- 広い電源電圧範囲:3.0V~5.5V
- 1.8V 互換のデジタル・ピン
- 過熱保護動作
- 4mm × 4mm × 0.9mm の QFN パッケージ (RGP) で 供給

## 2 アプリケーション

- 携帯電話 / スマートフォン
- タブレット
- 携帯型コンピュータ
- キーボードとマウス
- タッチ対応デバイス

## 3 概要

DRV8662 は、105V の昇圧スイッチ、パワー・ダイオード、完全差動アンプを内蔵したシングルチップのピエゾ・ハプティクス・ドライバです。この多用途デバイスは、高電圧と低電圧の両方のピエゾ・ハプティクス・アクチュエータを駆動できます。 差動とシングルエンドのどちらの入力信号も使用できます。 DRV8662 は、GPIO 制御のゲインとして28.8dB、34.8dB、38.4dB、40.7dB の 4 つをサポートしています。

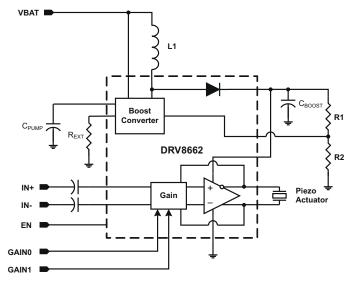
昇圧電圧は 2 つの外付け抵抗によって設定され、昇圧電流制限は R<sub>EXT</sub> 抵抗によりプログラム可能です。昇圧コンバータ・アーキテクチャでは、電源電流の要求が R<sub>EXT</sub> 抵抗で設定された制限を超えないため、DRV8662 はポータブル・アプリケーションに最適です。また、この機能により、ユーザーは希望の性能要件に基づき、特定のインダクタに合わせて DRV8662 回路を最適化できます。

DRV8662 は標準のスタートアップ時間が 1.5ms で、高速のハプティクス応答に理想的なピエゾ・ドライバです。熱過負荷保護機能により、過剰駆動によるデバイスの損傷が防止されます。

## 製品情報(1)

部品番号	パッケージ	本体サイズ (公称)
DRV8662	VQFN (20)	4.00mm × 4.00mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



概略回路図



## **Table of Contents**

1 特長	1 7.3 Feature Description	
2 アプリケーション	1 7.4 Device Functional Modes	10
3 概要	1 7.5 Programming	11
4 Revision History		12
5 Pin Configuration and Functions	3 8.1 Application Information	12
6 Specifications	4 8.2 Typical Application	
6.1 Absolute Maximum Ratings	4 9 Power Supply Recommendations	
6.2 ESD Ratings	4	
6.3 Recommended Operating Conditions	4 10.1 Layout Guidelines	
6.4 Thermal Information	5 10.2 Layout Example	
6.5 Electrical Characteristics	11 Device and Documentation Support	
6.6 Timing Requirements	5 11.1 Documentation Support	
6.7 Typical Characteristics		19
7 Detailed Description	8 12 Mechanical, Packaging, and Orderable	
7.1 Overview		19
7.2 Functional Block Diagram	8	
<b>4 Revision History</b> 資料番号末尾の英字は改訂を表しています。その最		Dama
Changes from Revision B (July 2014) to Revi		Page
<ul> <li>Changed V<sub>DD</sub> MIN spec from 3.0 to 3.3</li> </ul>		4
Changes from Revision A (November 2012) t	to Revision B (July 2014)	Page
• 「製品情報」表、「ESD 定格」表、「機能説明」セ	クション、「デバイスの機能モード」セクション、「アプリケー	ーションと実
装」セクション、「電源に関する推奨事項」セクショ	ョン、「レイアウト」セクション、「デバイスおよびドキュメント	のサポート」
	文情報」セクションを追加	
	e Recommend Operating Conditions table	
		•••••••
Changes from Revision * (June 2011) to Revi	ision A (November 2012)	Page

Added amplifier bandwidth spec (BW) to the Electrical Characteristics table for each gain setting......5

# **5 Pin Configuration and Functions**

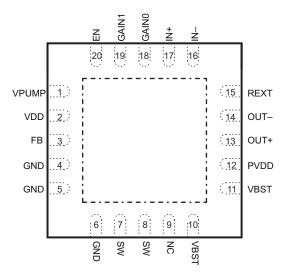


図 5-1. QFN (RGP) Top View

表 5-1. Pin Functions

	PIN	INPUT/ OUTPUT/	DESCRIPTION	
NAME	NO. (RGP)	POWER (I/O/P)	DESCRIPTION	
EN	20	I	Chip enable	
FB	3	1	Boost feedback	
GAIN0	18	I	Gain programming pin – LSB	
GAIN1	19	1	Gain programming pin – MSB	
GND	4, 5, 6	Р	Ground	
IN+	17	1	Non-inverting input (If unused, connect to GND through capacitor)	
IN-	16	1	Inverting input (If unused, connect to GND through capacitor)	
OUT+	13	0	Non-inverting output	
OUT-	14	0	Inverting output	
PVDD	12	Р	Amplifier supply voltage	
REXT	15	1	Resistor to ground, sets boost current limit	
SW	7, 8	Р	Internal boost switch pin	
VBST	10, 11	Р	Boost output voltage	
VDD	2	Р	Power supply (connect to battery)	
VPUMP	1	Р	Internal Charge-pump voltage	



## **6 Specifications**

## **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
	Supply voltage	VDD	-0.3	6.0	V
VI	Input voltage	IN+, IN–, EN, GAIN0, GAIN1, FB	-0.3	V <sub>DD</sub> +0.3	V
	Boost/Output Voltage	PVDD, SW, OUT+, OUT-		120	V
T <sub>A</sub>	Operating free-air temp	erature range	-40	70	°C
TJ	Operating junction temp	perature range	-40	150	°C
Sto	rage temperature, T <sub>stg</sub>		-65	85	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2500	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

				MIN	TYP	MAX	UNIT
$V_{DD}$	Supply voltage	VDD		3.3		5.5	V
V <sub>BST</sub>	Boost voltage	VBST		15		105	V
V <sub>IN</sub>	Differential input voltage				1.8 <sup>(1)</sup>		V
		VBST = 105 V, Frequency = 500	Hz, V <sub>O,PP</sub> = 200 V			50	
		VBST = 105 V, Frequency = 300 Hz, V <sub>O,PP</sub> = 200 V				100	
	Load capacitance	VBST = 80 V, Frequency = 300 Hz, V <sub>O,PP</sub> = 150 V				150	nF
CL		VBST = 55 V, Frequency = 300 Hz, V <sub>O,PP</sub> = 100 V				330	
		VBST = 30 V, Frequency = 300 Hz, V <sub>O,PP</sub> = 50 V				680	
		VBST = 25 V, Frequency = 300 F	Hz, V <sub>O,PP</sub> = 40 V			1	μF
		VBST = 15 V, Frequency = 300 F	Hz, V <sub>O,PP</sub> = 20 V			3	μι
V <sub>IL</sub>	Digital input low voltage	EN, GAIN0, GAIN1	V <sub>DD</sub> = 3.6 V			0.75	V
V <sub>IH</sub>	Digital input high voltage	EN, GAIN0, GAIN1	V <sub>DD</sub> = 3.6 V	1.4			V
R <sub>EXT</sub>	T Current limit control resistor			6		35	kΩ
L	Inductance for Boost Con	verter		3.3			μΗ

(1) Gains are optimized for a 1.8V peak input

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## **6.4 Thermal Information**

	THERMAL METRIC <sup>(1)</sup>	DRV8662	UNIT
	THERMAL METRIC	RGP (20 Pins)	UNII
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	33.1	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	30.9	
R <sub>0JB</sub>	Junction-to-board thermal resistance	8.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.4	C/VV
ΨЈВ	Junction-to-board characterization parameter	8.7	
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	2.5	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

## **6.5 Electrical Characteristics**

 $T_A$  = 25°C,  $V_{O,PP}$  =  $V_{OUT+}$  –  $V_{OUT-}$  = 200 V,  $C_L$  = 47 nF,  $A_V$  = 40 dB, L = 4.7  $\mu H$  (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT	
I <sub>IL</sub>	Digital input low current	EN, GAIN0, GAIN1	V <sub>DD</sub> = 3.6 V, V <sub>IN</sub> = 0 V			1	μA	
I <sub>IH</sub>	Digital input high current	EN, GAIN0, GAIN1	$V_{DD} = 3.6 \text{ V}, V_{IN} = V_{DD}$			5	μA	
I <sub>SD</sub>	Shut down current	V <sub>DD</sub> = 3.6 V, V <sub>EN</sub> = 0 V			13		μA	
		$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VB$	ST = 105 V, no signal		24		mA	
	Quiescent current	$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VB$	ST = 80 V, no signal		13		mA	
I <sub>DDQ</sub>	Quiescent current	V <sub>DD</sub> = 3.6 V, V <sub>EN</sub> = V <sub>DD</sub> , VB	ST = 55 V, no signal		9		mA	
		$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VB$	ST = 30 V, no signal		5		mA	
R <sub>IN</sub>	Input impedance	All gains			100		kΩ	
	Amplifier gain	GAIN<1:0> = 00			28.8			
_		GAIN<1:0> = 01		34.8			dB	
A <sub>V</sub>		GAIN<1:0> = 10			38.4		uБ	
		GAIN<1:0> = 11			40.7		ı	
		GAIN<1:0> = 00, V <sub>O,PP</sub> = 50	V, No Load		20			
BW	Amplifier Dandwidth	GAIN<1:0> = 01, V <sub>O,PP</sub> = 10	00 V, No Load		10		kHz	
DVV	Amplifier Bandwidth	GAIN<1:0> = 10, V <sub>O,PP</sub> = 15	50 V, No Load		7.5			
		GAIN<1:0> = 11, V <sub>O,PP</sub> = 20	00 V, No Load		5			
		V <sub>DD</sub> = 3.6 V, C <sub>L</sub> = 10 nF, f =	150 Hz, V <sub>O,PP</sub> = 200 V		75			
	Average battery current during	V <sub>DD</sub> = 3.6 V, C <sub>L</sub> = 10 nF, f =	300 Hz, V <sub>O,PP</sub> = 200 V		115		m 1	
I <sub>BAT</sub> , AVG	operation	V <sub>DD</sub> = 3.6 V, C <sub>L</sub> = 47 nF, f =	150 Hz, V <sub>O,PP</sub> = 200 V		210		mA	
		V <sub>DD</sub> = 3.6 V, C <sub>L</sub> = 47 nF, f =	300 Hz, V <sub>O,PP</sub> = 200 V		400			
THD+N	Total harmonic distortion plus noise	f = 300 Hz, V <sub>O,PP</sub> = 200 V			1%			

## 6.6 Timing Requirements

			MIN	TYP	MAX	UNIT
t <sub>SU</sub>	Start-up time	V <sub>DD</sub> = 3.6 V, time from EN high until boost and amplifier are fully enabled		1.5		ms

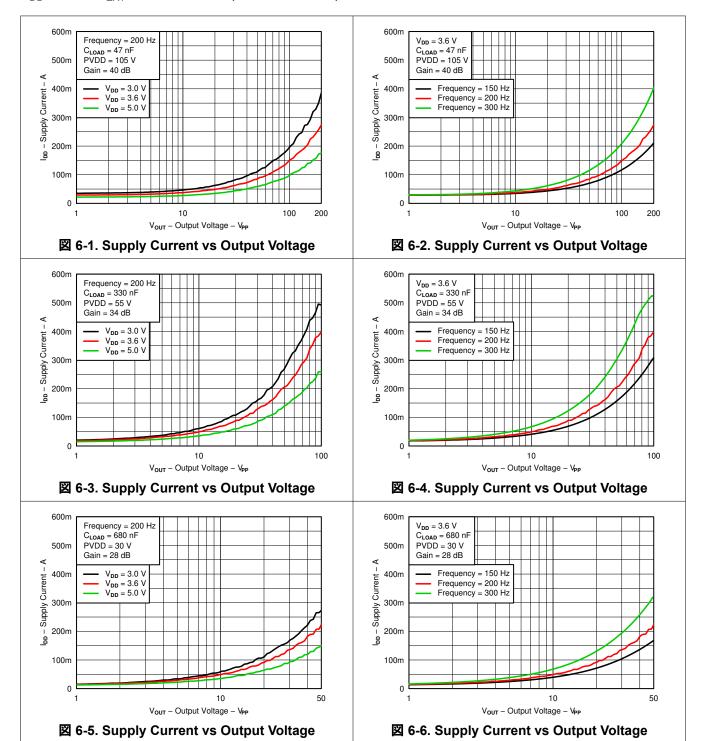
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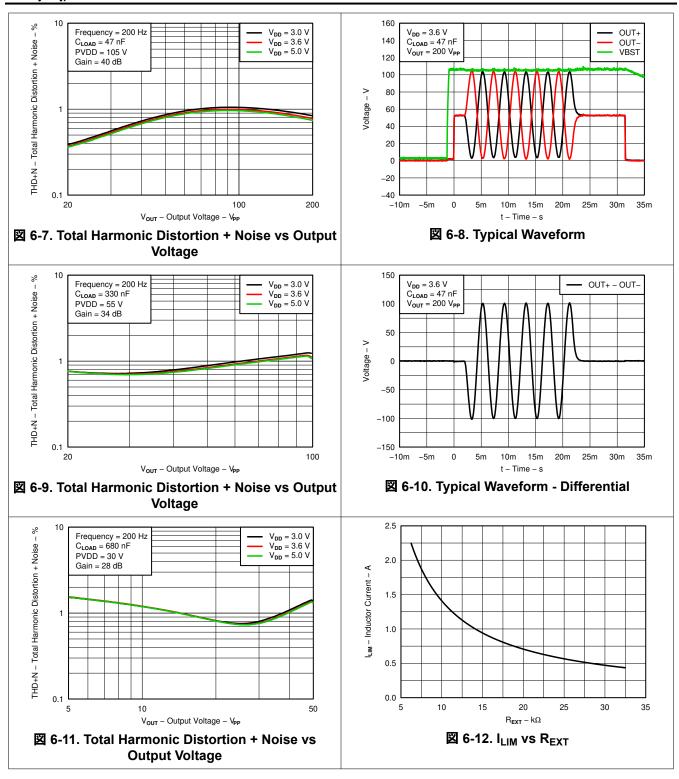


## **6.7 Typical Characteristics**

 $V_{DD}$  = 3.6 V,  $R_{EXT}$  = 7.5 k $\Omega$ , L = 4.7  $\mu$ H, Differential Input



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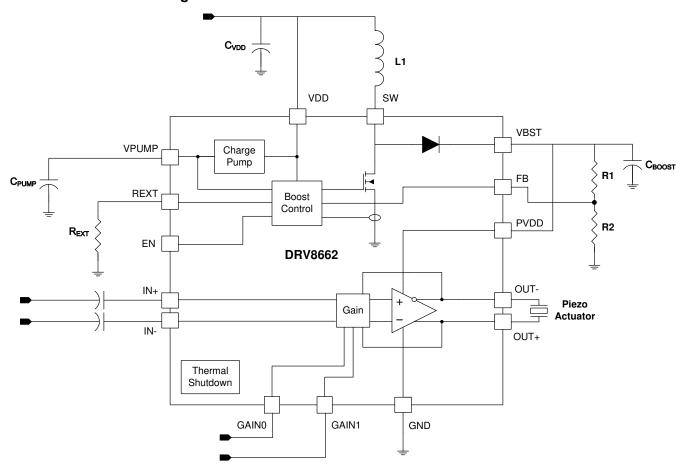


## 7 Detailed Description

## 7.1 Overview

The DRV8662 accepts the typical battery range used in portable applications (3.0 V to 5.5 V) and creates a boosted supply rail with an integrated DC-DC converter. This boosted supply rail is fed to an internal, high-voltage, fully-differential amplifier that is capable of driving capacitive loads such as piezos with signals up to 200  $V_{PP}$ . No transformer is required for boost operation. Only a single inductor is needed. The boost power FET and power diode are both integrated within the device.

## 7.2 Functional Block Diagram



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### 7.3 Feature Description

### 7.3.1 Fast Start-up (Enable Pin)

The DRV8662 features a fast startup time, which is essential for achieving low latency in haptic applications. When the EN pin transitions from low to high, the boost supply is turned on, the input capacitor is pre-charged, and the amplifier is enabled in a typical 1.5 ms total startup time. In the system application, the entire system latency should be kept to less than 30 ms total to be imperceptible to the end user. At 1.5 ms, the DRV8662 will be a small percentage of the total system latency.

#### 7.3.2 Gain Control

The gain from IN+/IN- to OUT+/OUT- is given by the table below.

GAIN1	GAIN0	Gain (dB)
0	0	28.8
0	1	34.8
1	0	38.4
1	1	40.7

The gains are optimized to achieve approximately 50  $V_{PP}$ , 100  $V_{PP}$ , 150  $V_{PP}$ , or 200  $V_{PP}$  at the output without clipping from a 1.8 V peak single-ended input signal source.

### 7.3.3 Adjustable Boost Voltage

The output voltage of the integrated boost converter may be adjusted by a resistive feedback divider between the boost output voltage (VBST) and the feedback pin (FB). The boost voltage should be programmed to a value greater than the maximum peak signal voltage that the user expects to create with the DRV8662 amplifier. Lower boost voltages will achieve better system efficiency when lower amplitude signals are applied, so the user should take care not to use a higher boost voltage than necessary. The maximum allowed boost voltage is 105V.

#### 7.3.4 Adjustable Boost Current Limit

The current limit of the boost switch may be adjusted via a resistor to ground placed on the REXT pin. The programmed current limit should be less than the rated saturation limit of the inductor selected by the user to avoid damage to both the inductor and the DRV8662. If the combination of the programmed limit and inductor saturation is not high enough, then the output current of the boost converter will not be high enough to regulate the boost output voltage under heavy load conditions. This will, in turn, cause the boosted rail to sag, possibly causing distortion of the output waveform.

### 7.3.5 Internal Charge Pump

The DRV8662 has an integrated charge pump to provide adequate gate drive for internal nodes. The output of this charge pump is placed on the VPUMP pin. An X5R or X7R storage capacitor of 0.1  $\mu$ F with a voltage rating of 10 V or greater must be placed at this pin.

### 7.3.6 Thermal Shutdown

The DRV8662 contains an internal temperature sensor that will shut down both the boost converter and the amplifier when the temperature threshold is exceeded. When the die temperature falls below the threshold, the device will restart operation automatically as long as the EN pin is high. Continuous operation of the DRV8662 is not recommended. Most haptic use models only operate the DRV8662 in short bursts. The thermal shutdown function will protect the DRV8662 from damage when overdriven, but usage models which drive the DRV8662 into thermal shutdown should always be avoided.

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#### 7.4 Device Functional Modes

### 7.4.1 Startup/shutdown Sequencing

A simple startup sequence should be employed to maintain smooth haptic operation. If the sequence is not followed, unintended haptic events or sounds my occur. Use the following steps to play back each haptic waveform.

#### 7.4.1.1 PWM Source

- 1. Send 50% duty cycle from the processor to the DRV8662 input filter. This is to allow the source and input filter to settle before the DRV8662 is fully enabled. At the same time (or on the next available processor cycle), transition the DRV8662 enable pin from logic low to logic high.
- 2. Wait 2 ms to ensure that the DRV8662 circuitry is fully enabled and settled.
- 3. Begin and complete playback of the haptic waveform. The haptic waveform PWM should end with a 50% duty cycle to bring the differential output back to 0 V.
- 4. Transition the DRV8662 enable pin from high to low and power down the PWM source.

#### 7.4.1.2 DAC Source

- 1. Set the DAC to its mid-scale code. This is to allow the source and input capacitors to settle before the DRV8662 is fully enabled. At the same time (or on the next available processor cycle), transition the DRV8662 enable pin from logic low to logic high.
- 2. Wait 2 ms to ensure that the DRV8662 circuitry is fully enabled and settled.
- 3. Begin and complete playback of the haptic waveform. The haptic waveform should end with a mid-scale DAC code to bring the differential output back to 0 V.
- 4. Transition the DRV8662 enable pin from high to low and power down the DAC source.

### 7.4.2 Low-voltage Operation

The lowest gain setting is optimized for 50 V<sub>PP</sub> with a boost voltage of 30 V. Some applications may not need 50 V<sub>PP</sub>, so the user may elect to program the boost converter as low as 15 V to improve efficiency. When using boost voltages lower than 30 V, some special considerations are in order. First, to reduce boost ripple to an acceptable level, a 50 V rated, 0.22 µF boost capacitor is recommended. Second, the full-scale input range may need adjustment to avoid clipping. Normally, a 1.8 V, single-ended PWM signal will give 50 VPP at the lowest gain. For example, if the boost voltage is set to 25 V for a 40 V<sub>PP</sub> full-scale output signal, the full-scale input range drops to 1.44 V for single-ended PWM inputs. An input voltage divider may be desired in this case if a 1.8V I/O is used as a PWM source.

Product Folder Links: DRV8662

### 7.5 Programming

### 7.5.1 Programming the Boost Voltage

The boost output voltage (VBST) is programmed via two external resistors as shown in 🗵 7-1.

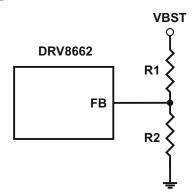


図 7-1. Boost Voltage Programming

The boost output voltage is given by 式 1:

$$V_{BOOST} = V_{FB} \left( 1 + \frac{R_1}{R_2} \right) \tag{1}$$

where  $V_{FB} = 1.32 \text{ V}$ .

VBST should be programmed to a value 5.0 V greater than the largest peak voltage expected in the system to allow adequate amplifier headroom. Since the programming range for the boost voltage extends to 105 V, the leakage current through the resistor divider can become significant. It is recommended that the sum of the resistance of R1 and R2 be greater than 500 k $\Omega$ . Note that when resistor values greater than 1 M $\Omega$  are used, PCB contamination may cause boost voltage inaccuracy. Exercise caution when soldering large resistances, and clean the area when finished for best results.

### 7.5.2 Programing the Boost Current Limit

The peak current drawn from the supply through the inductor is set solely by the  $R_{EXT}$  resistor. Note that this peak current limit is independent of the inductance value chosen, but the inductor should be capable of handling this programmed limit. The relationship of  $R_{EXT}$  to  $I_{LIM}$  is approximated by  $\pm$  2.

$$R_{EXT} = \left(K \frac{V_{REF}}{I_{LIM}}\right) - R_{INT}$$
 (2)

where K = 10500,  $V_{REF}$  = 1.35 V,  $R_{INT}$  = 60  $\Omega$ , and  $I_{LIM}$  is the desired peak current limit through the inductor.



## 8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The DRV8662 is typically used in systems that require haptic feedback using high-voltage Piezo actuators. These systems typically contain an applications processor or microcontroller, which generates a haptic waveform. This section contains two examples of such systems and how to appropriately configure the input signal for the DRV8662.

### 8.2 Typical Application

### 8.2.1 DRV8662 System Diagram with DAC Input

In the following DRV8662 diagram, the DRV8662 is configured with a differential DAC input and a generic Piezo actuator. This is useful for systems that have an available DAC or analog signal generator.

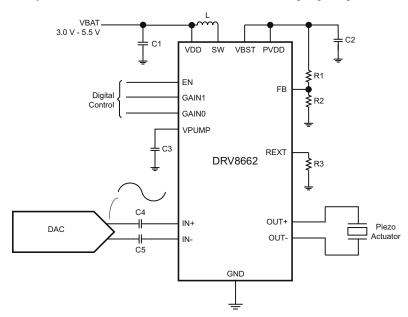


図 8-1. DRV8662 System Diagram with DAC Input

#### 8.2.1.1 Design Requirements

For this example, use the parameters shown in 表 8-1.

表 8-1. Design Requirements

DESIGN PARAMETER	EXAMPLE VALUE
VDD	3.0V – 5.5V
Boost Converter	20-105V
Output Voltage	2 x Boost Converter (Vpp)
Differential Input Voltage (IN+, IN-)	1.8Vp Sine wave

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表 8-2 contains a list of components required for configuring the DRV8662. The components labeled "Standard" can be used "as-is"; and, the components labeled "Configure" require the designer to evaluate specific system requirements.

表 8-2. List of Components

COMPONENT	DESCRIPTION	RECOMMENDED VALUE	UNIT	USE
CVDD VDD bypass capacitor		0.1	μF	Standard
CPUMP Voltage pump capacitor		0.1	μF	Standard
CIN+ / CIN- IN+ / IN- AC coupling capacitors		1	μF	Standard
REXT	Boost current limit resistor	See Programing the Boost Current Limit	Ω	Configure
CPVDD	Boost converter output capacitor	See Boost Capacitor Selection	μF	Configure
L	Boost converter inductor	See Inductor Selection	μΗ	Configure
R1	Boost converter high-side feedback resistor	See Programming the Boost Voltage	Ω	Configure
R2	Boost converter low-side feedback resistor	SeeProgramming the Boost Voltage	Ω	Configure

### 8.2.1.2 Detailed Design Procedure

#### 8.2.1.2.1 Inductor Selection

Inductor selection plays a critical role in the performance of the DRV8662. The range of recommended inductances is from 3.3 µH to 22 µH. In general, higher inductances within a given manufacturer's inductor series have lower saturation current limits, and vice-versa. When a larger inductance is chosen, the DRV8662 boost converter will automatically run at a lower switching frequency and incur less switching losses; however, larger values of inductance may have higher equivalent series resistance (ESR), which will increase the parasitic inductor losses. Since lower values of inductance generally have higher saturation currents, they are a better choice when attempting to maximize the output current of the boost converter. The following table has sample inductors that provide adequate performance.

For inductor recommendations, see DRV8662EVM User's Guide (SLOU319)

#### 8.2.1.2.2 Piezo Actuator Selection

There are several key specifications to consider when choosing a piezo actuator for haptics such as dimensions, blocking force, and displacement. However, the key electrical specifications from the driver perspective are voltage rating and capacitance. At the maximum frequency of 500 Hz, the DRV8662 is optimized to drive up to 50 nF at 200 V<sub>PP</sub>, which is the highest voltage swing capability. It will drive larger capacitances if the programmed boost voltage is lowered and/or the user limits the input frequency range to lower frequencies (e.g. 300 Hz).

For piezo actuator recommendations, see the DRV8662EVM User's Guide (SLOU319).

#### 8.2.1.2.3 Boost Capacitor Selection

The boost output voltage may be programmed as high as 105V. A capacitor with a voltage rating of at least the boost output voltage must be selected. Since ceramic capacitors tend to come in ratings of 100 V or 250 V, a 250 V rated 100 nF capacitor of the X5R or X7R type is recommended for the 105 V case. The selected capacitor should have a minimum working capacitance of at least 50 nF.

#### 8.2.1.2.4 Current Consumption Calculation

It is useful to understand how the voltage driven onto a piezo actuator relates to the current consumption from the power supply. Modeling a piezo element as a pure capacitor is reasonably accurate. The equation for the current through a capacitor for an applied sinusoid is given by 式 3:

$$I_{Capacitor(Peak)} = 2\pi \times f \times C \times V_P$$

(3)



where f is the frequency of the sinusoid in Hz, C is the capacitance of the piezo load in farads, and  $V_P$  is the peak voltage. At the power supply (usually a battery), the actuator current is multiplied by the boost-supply ratio and divided by the efficiency of the boost converter as shown by  $\pm 4$ .

$$I_{BAT(Peak)} = 2\pi \times f \times C \times V_P \times \frac{V_{Boost}}{V_{BAT} \times \mu_{Boost}}$$
(4)

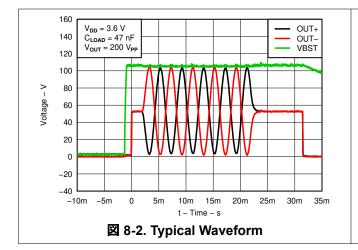
Substituting typical values for the variables of this equation yields a typical peak current seen by the battery with a sine input as in  $\pm 5$ .

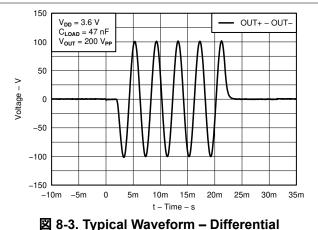
$$I_{BAT(Peak)} = 2\pi \times 300 \text{ Hz} \times 50 \text{ nF} \times 100 \times \frac{105}{3.6 \times 0.7} = 392 \text{ mA}$$
 (5)

#### 8.2.1.2.5 Input Filter Considerations

Depending on the quality of the source signal provided to the DRV8662, an input filter may be required. Some key factors to consider are whether the source is generated from a DAC or from PWM and the out-of-band content generated. If proper anti-image rejection filtering is used to eliminate image components, the filter can possibly be eliminated depending on the magnitude of the out-of-band components. If PWM is used, at least a 1<sup>st</sup> order RC filter is required. The PWM sample rate should be greater than 30 kHz to keep the PWM ripple from reaching the piezo element and dissipating unnecessary power. A 2<sup>nd</sup> order RC filter may be desirable to further eliminate out-of-band signal content to further drive down power dissipation and eliminate audible noise.

### 8.2.1.3 Application Curves





### 8.2.2 DRV8662 System Diagram with Filtered Single-Ended PWM Input

The DRV8662 can be used with a PWM input signal for systems that do not have an available DAC or analog output. Most piezo actuator systems require a PWM input filter to remove any unwanted noise.

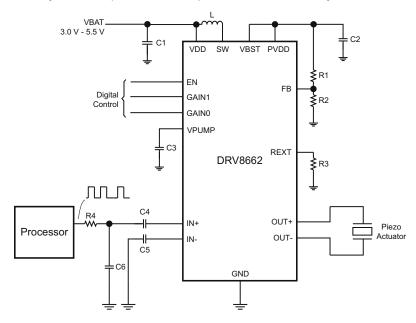


図 8-4. DRV8662 System Diagram with Filtered Single-Ended PWM Input

#### 8.2.2.1 Design Requirements

For this example, use the parameters shown in 表 8-3.

表 8-3. Design Requirements

DESIGN PARAMETER	EXAMPLE VALUE
VDD	3.0V – 5.5V
Boost Converter	20-105V
Output Voltage	2 x Boost Converter (Vpp)
Differential Input Voltage (IN+, IN-)	1.8Vp PWM

表 8-4 contains a list of components required for configuring the DRV8662. The components labeled "Standard" can be used "as-is"; and, the components labeled "Configure" require the designer to evaluate specific system requirements.

表 8-4. List of Components

COMPONENT	DESCRIPTION	RECOMMENDED VALUE	UNIT	USE			
CVDD	VDD bypass capacitor	0.1	μF	Standard			
CPUMP	Voltage pump capacitor	0.1	μF	Standard			
CIN+ / CIN-	IN+ / IN- AC coupling capacitors	1	μF	Standard			
REXT	Boost current limit resistor	See Programing the Boost Current Limit	Ω	Configure			
CPVDD	Boost converter output capacitor	See Boost Capacitor Selection	μF	Configure			
L	Boost converter inductor	See Inductor Selection	μH	Configure			
R1	Boost converter high-side feedback resistor	See Programming the Boost Voltage	Ω	Configure			

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### 表 8-4. List of Components (continued)

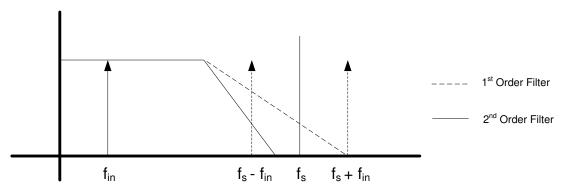
COMPONENT	DESCRIPTION	RECOMMENDED VALUE	UNIT	USE
R2	Boost converter low-side feedback resistor	SeeProgramming the Boost Voltage	Ω	Configure

#### 8.2.2.2 Detailed Design Procedure

Use the following section for designing the DRV8662 input filter. See the *DRV8662 System with DAC Input Detailed Design Procedure* for the remaining design.

#### 8.2.2.2.1 Input Filter Design

When using a PWM input, a low-pass filter is required. The primary parameters for determining the input filter are the PWM input frequency and sample rate. Because haptic waveforms are typically less than 500Hz, the input filter must attenuate frequencies above 500 Hz. For samples rates above 20 kHz, a simple first-order RC filter is recommended; however, for sample rates much lower (such as 8 kHz), a first-order filter may not sufficiently attenuate the high-frequency content. Thus, for lower sampling rates, a second-order RC filter may be required. The *DRV8662EVM User's Guide* contains example filter configurations for both first-order and second-order filters. The DRV8662EVM default configuration uses a second-order, differential filter, but it can be replaced by a first-order, single-ended or differential filter.



Apply these criteria to select an input filter:

- 1. First-order RC filters, both single-ended and differential, are recommended for 20 kHz and higher data sample rates. The first-order filters have adequate settling time and the fewest components.
- 2. Second-order filters are recommended for noiseless operation when using a lower data sample rate where a sharper cutoff is necessary.
- 3. The attenuation at the PWM carrier frequency should be at least -40 dB for haptic applications.

### 8.2.2.3 Application Curves

See DRV8662 System with DAC Input Application Curves.

## 9 Power Supply Recommendations

The recommended voltage supply range for the DRV8662 is 2.3V to 5.5V. For proper operation, place a  $0.1\mu F$  low equivalent series resistance (ESR) supply-bypass capacitor of X5R or X7R type near the VDD pin with a voltage rating of at least 10V.

The internal charge pump requires a  $0.1\mu F$  capacitor of X5R or X7R type with a voltage rating of 10V or greater be placed between the VPUMP pin and GND for proper operation and stability. Do not use the charge pump as a voltage source for any other devices.



### 10 Layout

## 10.1 Layout Guidelines

- To achieve optimum device performance, use of the thermal footprint outlined by this datasheet is recommended. See land pattern diagram for exact dimensions. The DRV8662 power pad must be soldered directly to the thermal pad on the printed circuit board. The printed circuit board thermal pad should be connected to the ground net with thermal vias to any existing backside/internal copper ground planes. Connection to a ground plane on the top layer near the corners of the device is also recommended.
- Another key layout consideration is to keep the boost programming resistors (R1 and R2) as close as
  possible to the FB pin of the DRV8662. Care should be taken to avoid getting the FB trace near the SW
  trace.

## 10.2 Layout Example

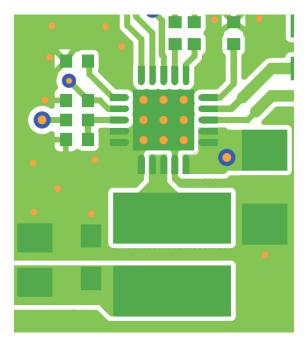


図 10-1. Layout Example

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## 11 Device and Documentation Support

## 11.1 Documentation Support

#### 11.1.1 Related Documentation

DRV8662EVM User's Guide (SLOU319)

DRV8662 Configuration Guide (SLOA198)

### 11.2 Trademarks

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## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
	(1)	(2)			(3)	(4)	(5)		(0)
DRV8662RGPR	Active	Production	QFN (RGP)   20	3000   LARGE T&R	Yes	Call TI   Nipdau	Level-4-260C-72 HR	-40 to 70	8662
DRV8662RGPR.A	Active	Production	QFN (RGP)   20	3000   LARGE T&R	Yes	Call TI	Level-4-260C-72 HR	-40 to 70	8662
DRV8662RGPT	Active	Production	QFN (RGP)   20	250   SMALL T&R	Yes	NIPDAU	Level-4-260C-72 HR	-40 to 70	8662
DRV8662RGPT.A	Active	Production	QFN (RGP)   20	250   SMALL T&R	Yes	NIPDAU	Level-4-260C-72 HR	-40 to 70	8662

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

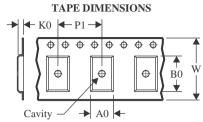
<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

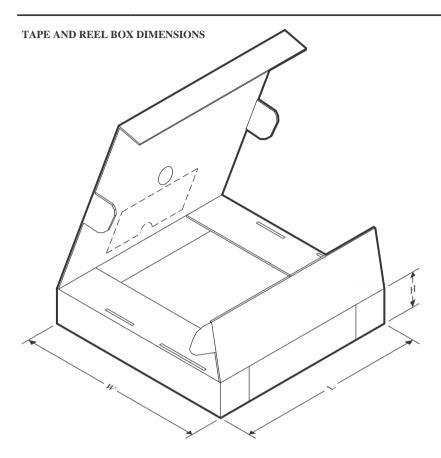
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8662RGPR	QFN	RGP	20	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
DRV8662RGPT	QFN	RGP	20	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

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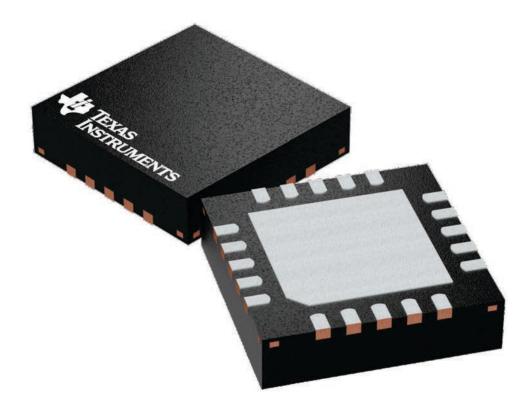


### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8662RGPR	QFN	RGP	20	3000	346.0	346.0	33.0
DRV8662RGPT	QFN	RGP	20	250	210.0	185.0	35.0

4 x 4, 0.5 mm pitch

VERY THIN QUAD FLATPACK



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

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